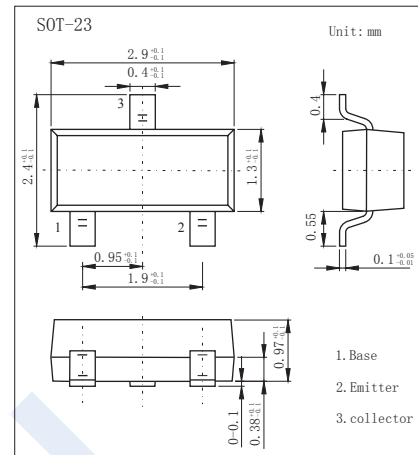


PNP Transistors

2SA1035

■ Features

- Low noise voltage NV.
- High forward current transfer ratio hFE.
- Complementary to 2SC2406.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	-55	V
Collector-emitter voltage	V _{CEO}	-55	V
Emitter-base voltage	V _{EB0}	-5	V
Collector current	I _c	-50	mA
Peak collector current	I _{CP}	-100	mA
Collector power dissipation	P _c	200	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CB0}	I _c = -100 μA, I _E =0	-55			V
Collector- emitter breakdown voltage	V _{CEO}	I _c = -2 mA, I _B =0	-55			
Emitter - base breakdown voltage	V _{EB0}	I _E = -100 μA, I _c =0	-5			
Collector-base cut-off current	I _{CB0}	V _{CB} = -50 V, I _E =0			-100	nA
Collector- emitter cut-off current	I _{CEO}	V _{CE} = -40 V, I _B =0			-1	μA
Emitter cut-off current	I _{EB0}	V _{EB} = -5V, I _c =0			-100	nA
Collector-emitter saturation voltage	V _{CE(sat)}	I _c =-100 mA, I _B =-10mA			-0.6	V
Base - emitter saturation voltage	V _{BE(sat)}	I _c =-100 mA, I _B =-10mA			-1.2	
Base - emitter voltage	V _{BE}	V _{BE} =-1V, I _c =-100mA			-1.0	
DC current gain	h _{FE}	V _{CE} = -5V, I _c = -2mA	180		700	
Noise voltage	NV	V _{CE} = -10V, I _c = -1mA, G _v = 80dB R _g = 100kΩ, Function = FLAT			150	mV
Transition frequency	f _r	V _{CB} = -5V, I _E = -2mA, f=200MHz		200		MHz

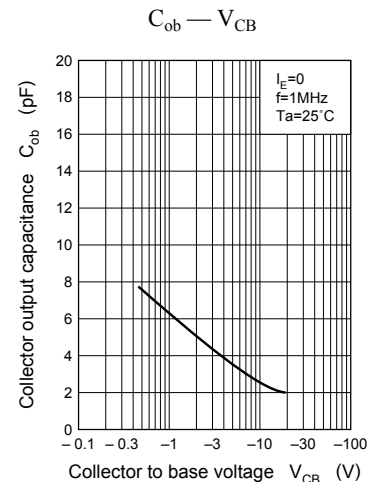
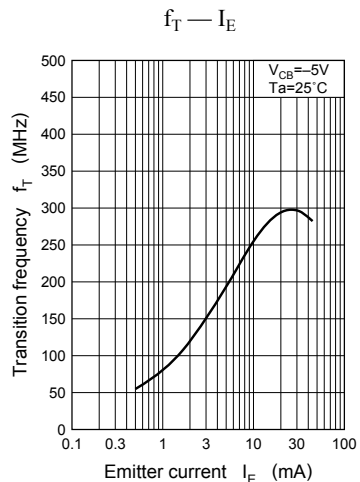
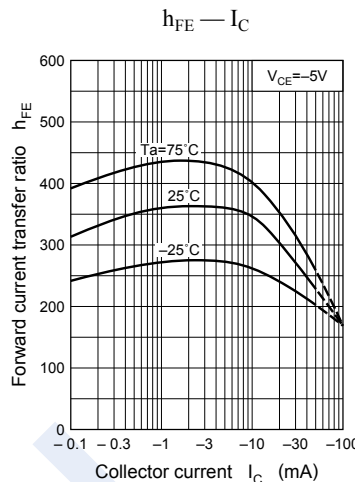
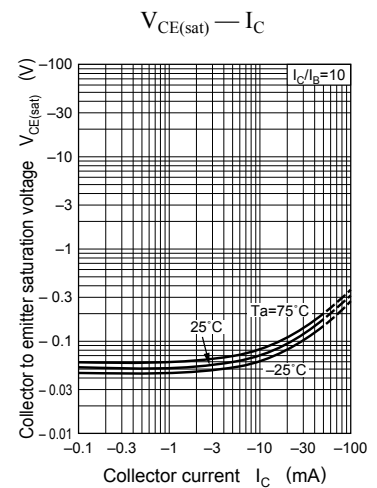
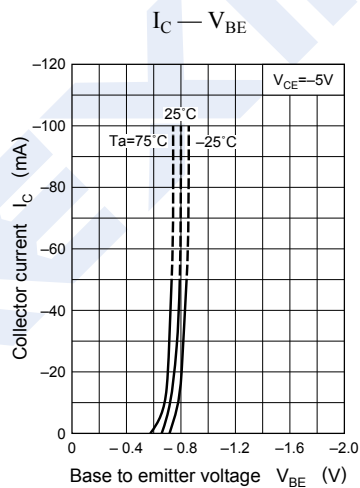
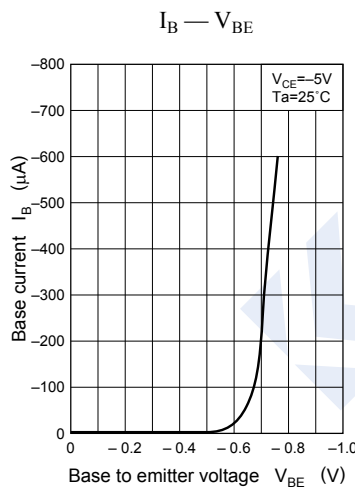
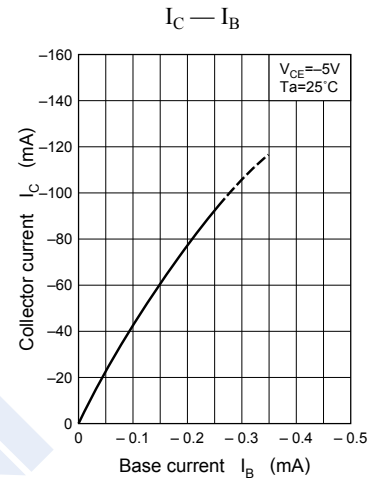
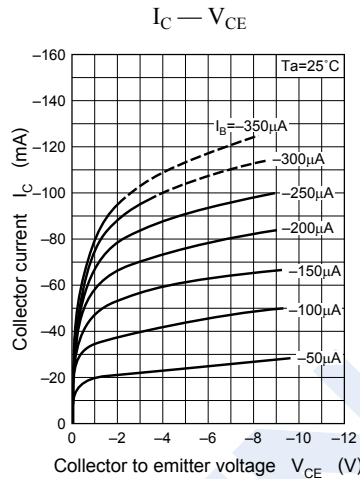
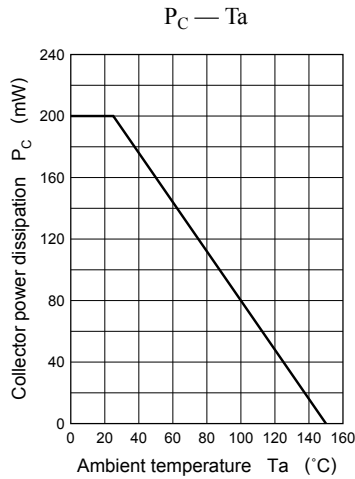
hFE Classification

Marking	HR	HS	HT
hFE	180~360	260~520	360~700

PNP Transistors

2SA1035

■ Typical Characteristics



PNP Transistors 2SA1035

■ Typical Characteristics

